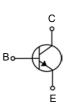


Features

- Collector Current: I_C=0.6A
- Power Dissipation of 300mW



SOT-23

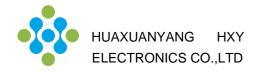


Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
SMMBT2222ALT1G	SOT-23	1P	3000

Maximum Ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V _{CBO}	75	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current	I _C	600	mA
Collector Power Dissipation	P _C	300	mW
Thermal Resistance From Junction To Ambient	$R_{\Theta JA}$	417	°CW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	- 55∼+150	°C

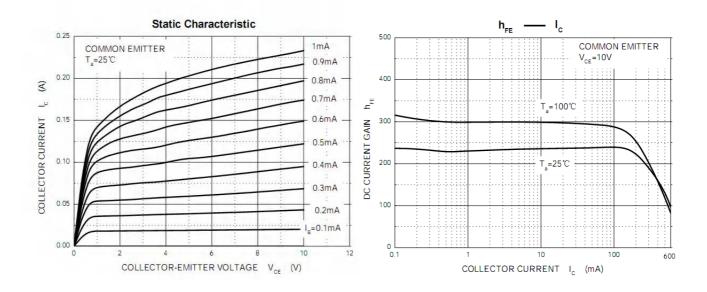


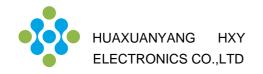
Electrical Characteristics (Ta=25°C unless otherwise specified)

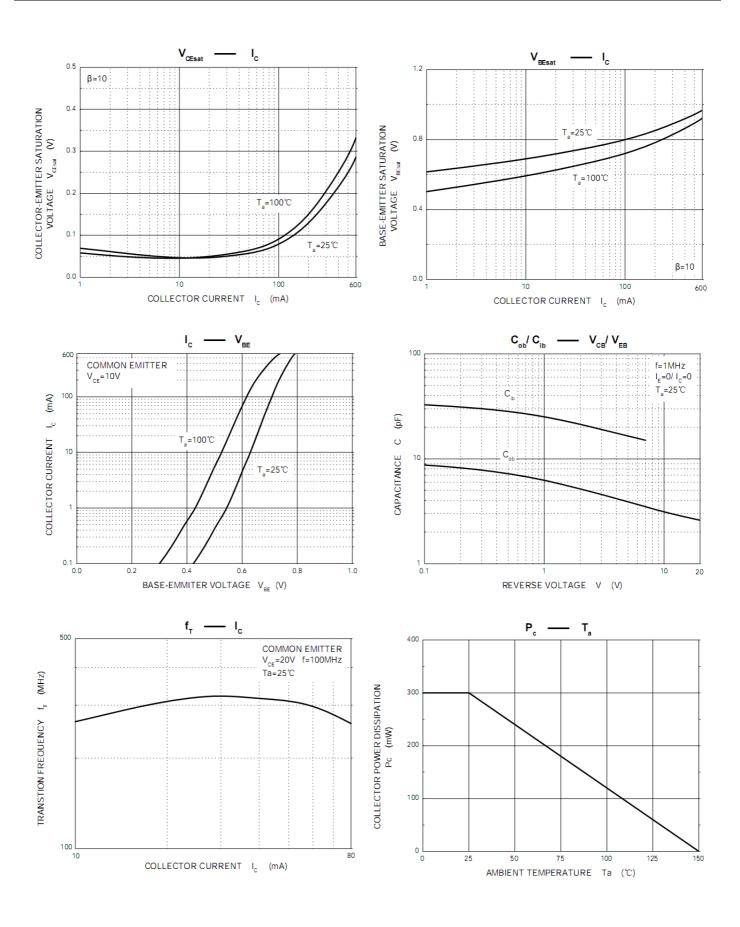
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E =0	75			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _C = 10mA, I _B =0	40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0			0.01	μA
Collector cut-off current	I _{CEX}	V _{CE} =30V,V _{BE(off)} =3V			0.01	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 3V, I _C =0			0.1	μA
	h _{FE(1)} *	V _{CE} =10V, I _C = 150mA	200		300	
DC current gain	h _{FE(2)}	V _{CE} =10V, I _C = 0.1mA	40			
	h _{FE(3)} *	V _{CE} =10V, I _C = 500mA	42			
Collector-emitter saturation voltage	V _{CE(sat)} *	I_C =500 mA, I_B = 50mA I_C =150 mA, I_B =15mA			1 0.3	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =500 mA, I _B = 50mA I _C =150 mA, I _B =15mA			2.0 1.2	V
Transition frequency	f⊤	V _{CE} =20V, I _C = 20mA, f=100MHz	300			MHz
Delay time	t _d	V _{CC} =30V, V _{BE(off)} =-0.5V			10	ns
Rise time	t _r	I _C =150mA , I _{B1} = 15mA			25	ns
Storage time	ts	V _{CC} =30V, I _C =150mA			225	ns
Fall time	t _f	I _{B1} =-I _{B2} =15mA			60	ns

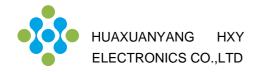
^{*}pulse test: Pulse Width ≤300µs, Duty Cycle≤ 2.0%.

Typical Characteristics

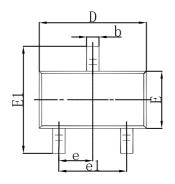


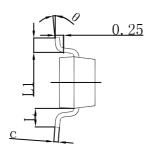


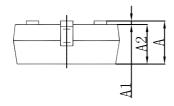




SOT-23 Package Outline Dimensions

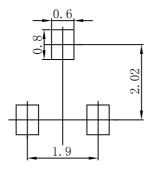






Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950) TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



- 1.Controlling dimension:in millimeters. 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

SMMBT2222ALT1G NPN Plastic-Encapsulate Transistors

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